

*ABSTRACT AMENDMENTS*

Replace the Abstract with:

A semiconductor laser device has an n-GaAs substrate ~~(1)~~. On the n-GaAs substrate ~~(1)~~, by turns, are an n-AlGaInP ~~clad~~ cladding layer ~~(2)~~, an AlGaInP/GaInP MQW active layer ~~(3)~~, a p-AlGaInP first ~~clad~~ cladding layer ~~(4)~~, a single layer p-Al<sub>x</sub>Ga<sub>1-x</sub>As-ESL ~~(5)~~ of a single layer etching stopping layer, a p-AlGaInP second ~~clad~~ cladding layer ~~(7)~~ with a stripe-form protrusion ~~(6)~~, and a p-GaAs contact layer ~~(8)~~ are provided. The portion, other than the stripe-form protrusion ~~(6)~~, of the p-AlGaInP second ~~clad~~ cladding layer ~~(7)~~ is covered with an ~~insulative~~ insulating film ~~(9)~~. The refractive index of the p-Al<sub>x</sub>Ga<sub>1-x</sub>As-ESL ~~(5)~~ is nearly equal to the refractive index of each of the ~~clad~~ lower, first upper, and second upper cladding layers ~~(2), (4) and (7)~~.